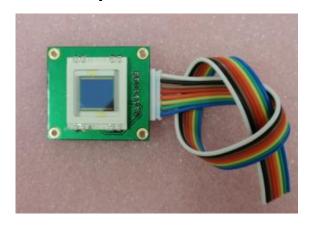
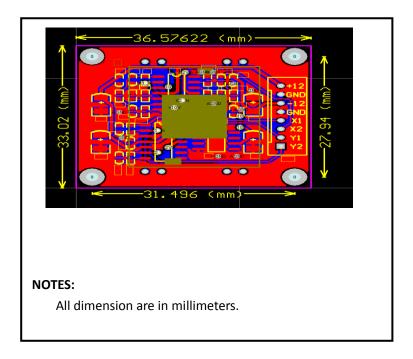




Two-dimensional PSD with I/V Amplifier





Description

The PSD100-SPB is a 10mm*10mm dual axis position sensing diode on a PCB with I/V amplifiers. It also contains circuitry for applying a 5V bias voltage to the position sensing diode, or the customer can externally apply a bias voltage. This module can be connected to Voltmeter, oscilloscope, A/D card or PC via USB cable.

Features

- * Both DC and AC light can work well.
- * Operating temperature is from -40 to +100 $^{\circ}\mathrm{C}$
- * Storage temperature is from -40 to +100 $^{\circ}\mathrm{C}$

Applications

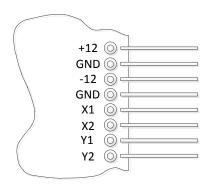
- * NIR & Visible pulsed light position and tracking
- * Range finder
- *Length measurement

- * Laser beam tracking
- * 3D measurement
- * Distortion measurement

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice

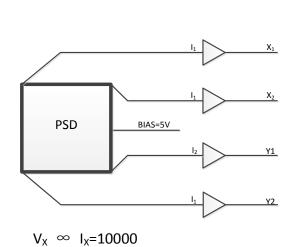


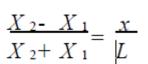
Connection: (bottom layer)

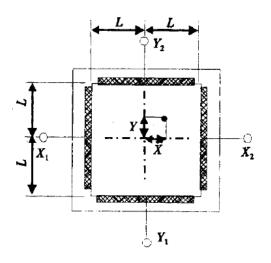


Symbol	Characteristic	Min.	Max.	Тур.	Unit
Y1	Y1 output voltage	-V _S +3	V _S -3	/	V
Y2	Y2 output voltage	-V _S +3	V _S -3	/	V
X1	X1 output voltage	-V _S +3	V _S -3	/	V
X2	X2 output voltage	-V _S +3	V _S -3	/	V
GND	GND	0	0	0	V
-12	-Vs, power supply voltage	-18	-4.5	-12	V
GND	GND	0	0	0	V
+12	+Vs, power supply voltage	+18	+4.5	+12	V

Block Diagram:







$$\frac{Y_2 - Y_1}{Y_2 + Y_1} = \frac{y}{L}$$

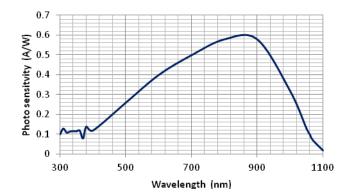
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ELECTRO OPTICAL CHARACTERISTICS:

Symbol	Characteristic	Test Conditions	Min.	Max.	Тур.	Unit
Vo	Output voltage	$V_S=\pm 12V$, $VR=5V$	-V _S +3	+V _S -3	/	V
Io	Output current	$V_S=\pm 12V$, $VR=5V$	/	/	25	mA
	Theoretical noise	$V_S=\pm 12V$, $VR=5V$	/	/	15	nV/ √ Hz
f _{3dB}	3dB bandwidth	$V_S=\pm 12V$, $VR=5V$	/	/	250	kHz
Vs	Power supply voltage		±11	±18	±12	V
Vr	Applied Bias Voltage		0	12	10	V
Tstg	Storage Temp		-15	+100	+25	$^{\circ}$
Тор	Operating Temp		0	+70	+25	$^{\circ}$

PSD Characteristics:



Parameter	Symbol	Min.	Тур.	Max.	Unit
Active area			10 x 10		mm²
Position non-linearity			0,3	0,8	%(±)
Detector resistance	Rdet	7	10	16	$k\Omega$
Dark current	Id		100	500	nA
Noise current	Inoise		1,3	2,5	pA/√Hz
Responsivity	r		0,63		A/W
Capacitance	Cj		90	110	pF
Rise time (10-90%)	tr		400	800	ns
Reverse voltage (bias)	Vr	5	15	20	V
Thermal drift			40	200	ppm/°C
Maximum ratings					
Reverse voltage	VR-max			30	V
Operating temperature	Toper			70	°C
Storage temperature	Tstg			100	°C

Test conditions: Room temperature 23°C. Reverse voltage 15 V. Light-source wavelength 940 nm.

Position non-linearity and thermal drift are valid within 80% of the detector length.

Ceramic substrate, 25,0 x 21,0 mm², with solderable pins and protective window.

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